

## Equipments &amp; Materials

**Thermo VG Semicon** (East Grinstead, UK) has received an order for a V90 MBE system from the National Research Council of Canada (for scientists at its Institute for Microstructural Sciences to develop opto and high-speed electronic devices).

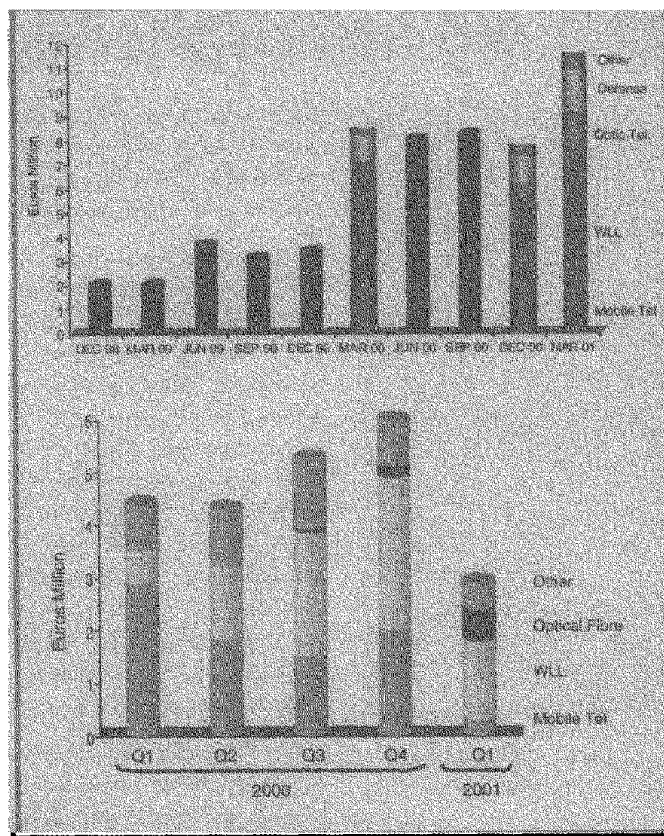
Despite fiscal 2001 sales (to end-March) of US\$38.2m (up 45% on fiscal 2000), Q4/2001 sales for plasma etch tool supplier **Tegal Corp** (Petaluma, CA, USA) were only US\$6.2m (46% down on Q3 and 27% on Q4/2000). However, order backlog is higher than in the past four years, so it expects net income at or near the break-even for the June quarter.

**KDF** (Rockleigh, NJ, USA) has shipped its 954NT four-target PVD in-line batch sputtering system to the newly established **Marconi Optical Components** group (Caswell, UK) for GaAs manufacturing, via its European representative **TLCsrl Equipment & Assets** (Milan, Italy).

**VIGO Systems Ltd** (Warsaw, Poland) - which manufactures uncooled photoconductors, photodiodes and photoelectromagnetic 10.6  $\mu\text{m}$  HgCdTe radiation detectors - has installed a **domnick hunter MAXIGAS** nitrogen gas generator for its MOCVD growth.

**StratEdge** (San Diego, CA, USA; Tel: +1-858-569-5000) is now offering complete assembly and test services of DC-50 GHz devices (both fibre-optic and MMIC). It has also launched the 580403 26-31 GHz leaded package for Ka-band operation (joining its DC-23 GHz leaded packages).

## Picogiga sees shift to Wireless Local Loop



For epiwafer foundry **Picogiga** Q1/2001 revenues were €3.3m. This is down 23% on Q1/2000:

- down 60% in the US, but up 80% in Asia and Europe;
- down 90% in wireless, but up 115% in Wireless Local Loop (and a breakthrough in fibre-optic telecoms, which did not exist one year ago).

New sales for InGaP HBTs reached €0.4m, but could have tripled without a two-month delay to the installation of a multi-wafer MBE system. Order backlog grew from a record €8m at end-2000 to €12m at end-March.

Growth in second-half 2001 should make 2001 revenues higher than last year, reckons chairman and CEO **Linh Nuyen**.

Graph showing the decline of wireless revenues and the rise of Wireless Local Loop revenues for Picogiga.

## Procomp increases GaAs focus

In Q1/2001 GaAs epi-wafers contributed 21% of total sales for **Procomp Informatics Ltd** (Hsinchu, Taiwan) compared to 14% (NT\$985m) in 2000. By end-2001 they are expected to contribute 33% (NT\$2.61bn).

Once compound semiconductors make up half of all revenues (in 2002), Procomp will spin off its broadband communications division as an independent subsidiary.

About 60% of Procomp's epi-wafer line is for cell-phone applications - NT\$411m in Q1/2001 (up 198% year-on-year). New GaAs processing equipment that arrived in Q1 should be on-line in three months.

## AXT maintains growth

For Q1/2001 **AXT Inc** (Fremont, CA, USA) had record revenues for continuing operations of US\$40.1m (up 80% Q1/2000 and 8% on Q4/2000):

- Substrate division (97% of sales) US\$38.8m (up 103% and 7%, respectively, primarily due to large-diameter GaAs and InP substrates, says president and CEO **Morris Young**). InP sales grew 36% on Q4/2000 and are now nearly 20% of substrate sales. "Demand will continue to increase as next-generation

fibre-optic components currently under development require even higher power and higher frequency capabilities," says Young.

- Visible emitter division (3% of sales) US\$1.3m (up 28% on Q4/2000), with VCSEL market growth fuelled by demand for higher data transmission rates in fibre-optic communications.

AXT expects Q2/2001 sales to be 2-6% up on Q1. "We believe we are on track for another record year," adds Young.

## First commercial 3" GaN epi-wafers

**Technologies and Devices International Inc** (Gaithersburg, MD, USA) is offering (from July) the industry's first commercially available 3" GaN epi-wafers on sapphire substrate. This complements its existing 2" GaN and AlN epi-wafers (on both sapphire and SiC substrates).

TDI is also developing next generation epi-wafers comprising multi-layer device structures for short wavelength optoelectronic, high-power communication, and power electronic applications (as well as its program to commercialise bulk GaN and AlN substrates).